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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, IrDA, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	56
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 20x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-FQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk22dn512vlk5

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

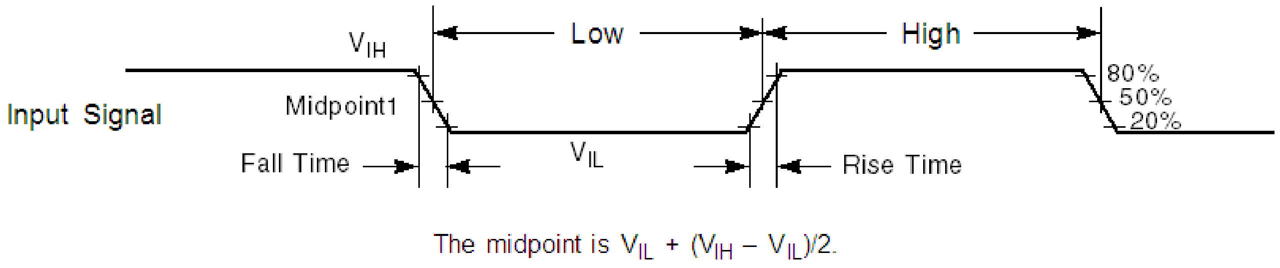

Figure 1. Input signal measurement reference

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage				
	• $2.7 V \leq V_{DD} \leq 3.6 V$	$0.7 \times V_{DD}$	—	V	
	• $1.7 V \leq V_{DD} \leq 2.7 V$	$0.75 \times V_{DD}$	—	V	
V_{IL}	Input low voltage				
	• $2.7 V \leq V_{DD} \leq 3.6 V$	—	$0.35 \times V_{DD}$	V	
	• $1.7 V \leq V_{DD} \leq 2.7 V$	—	$0.3 \times V_{DD}$	V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICIO}	I/O pin DC injection current — single pin				1
	• $V_{IN} < V_{SS}$-0.3V (Negative current injection)	-3	—	mA	
	• $V_{IN} > V_{DD}$+0.3V (Positive current injection)	—	+3		

Table continues on the next page...

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than V_{AIO_MIN} or greater than V_{AIO_MAX}, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO\_MIN}-V_{IN})/|I_{ICAIO}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO\_MAX})/|I_{ICAIO}|$. Select the larger of these two calculated resistances if the pin is exposed to positive and negative injection currents.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					3, 4
	- @ 1.8 V	—	17.04	19.3	mA	
	- @ 3.0 V					
	- @ 25°C	—	17.01	18.9	mA	
	- @ 125°C	—	19.8	21.3	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	7.95	9.5	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	5.88	7.4	mA	5
I_{DD_STOP}	Stop mode current at 3.0 V	—			μA	
	- @ –40 to 25°C		320	436		
	- @ 50°C		360	489		
	- @ 70°C		410	620		
	- @ 105°C		610	1100		
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	754	—	μA	6
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	1.1	—	mA	7
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V	—	437	—	μA	8
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V	—			μA	
	- @ –40 to 25°C		7.33	24.2		
	- @ 50°C		14	32		
	- @ 70°C		28	48		
	- @ 105°C		110	280		
I_{DD_LLS}	Low leakage stop mode current at 3.0 V	—			μA	
	- @ –40 to 25°C		3.14	4.8		
	- @ 50°C		6.48	28.3		
	- @ 70°C		13.85	44.6		
	- @ 105°C		55.53	71.3		
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V				μA	
	- @ –40 to 25°C	—	2.19	3.4		
	- @ 50°C		4.35	4.35		
	- @ 70°C		8.92	24.6		
	- @ 105°C		35.33	45.3		
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V	—			μA	
	- @ –40 to 25°C		1.77	3.1		
	- @ 50°C		2.81	13.8		
	- @ 70°C		5.20	22.3		
	- @ 105°C		19.88	34.2		

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	1.03 1.92 4.03 17.43	1.8 7.5 15.9 28.7	μA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.543 1.36 3.39 16.52	1.1 7.58 14.3 24.1	μA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.359 1.03 2.87 15.20	0.95 6.8 15.4 25.3	μA	
I_{DD_VBAT}	Average current when CPU is not accessing RTC registers at 3.0 V • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.91 1.1 1.5 4.3	1.1 1.35 1.85 5.7	μA	9

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks disabled.
3. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled, and peripherals are in active operation.
4. Max values are measured with CPU executing DSP instructions
5. 25 MHz core and system clock, 25 MHz bus clock, and 12.5 MHz flash clock. MCG configured for FEI mode.
6. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
7. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing from flash.
8. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.
9. Includes 32 kHz oscillator current and RTC operation.

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL

Table 14. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
J_{cyc_fll}	FLL period jitter • f_{DCO} = 48 MHz • f_{DCO} = 98 MHz	— —	180 150	— —	ps	
$t_{fll\_acquire}$	FLL target frequency acquisition time	—	—	1	ms	7
PLL						
f_{vco}	VCO operating frequency	48.0	—	100	MHz	
I_{pll}	PLL operating current • PLL @ 96 MHz ($f_{osc\_hi\_1}$ = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 48)	—	1060	—	µA	8
I_{pll}	PLL operating current • PLL @ 48 MHz ($f_{osc\_hi\_1}$ = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 24)	—	600	—	µA	8
f_{pll_ref}	PLL reference frequency range	2.0	—	4.0	MHz	
J_{cyc_pll}	PLL period jitter (RMS) • f_{vco} = 48 MHz • f_{vco} = 100 MHz	— —	120 50	— —	ps ps	9
J_{acc_pll}	PLL accumulated jitter over 1µs (RMS) • f_{vco} = 48 MHz • f_{vco} = 100 MHz	— —	1350 600	— —	ps ps	9
D_{lock}	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	
D_{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t_{pll_lock}	Lock detector detection time	—	—	$150 \times 10^{-6} + 1075(1/f_{pll\_ref})$	s	10

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. 2 V <= VDD <= 3.6 V.
3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
4. The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature should be considered.
5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
7. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
8. Excludes any oscillator currents that are also consuming power while PLL is in operation.
9. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
10. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

6.3.2 Oscillator electrical specifications

6.3.2.1 Oscillator DC electrical specifications

Table 15. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	μA	
	• 8 MHz (RANGE=01)	—	300	—	μA	
	• 16 MHz	—	950	—	μA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high-gain mode (HGO=1)					1
	• 32 kHz	—	25	—	μA	
	• 4 MHz	—	400	—	μA	
	• 8 MHz (RANGE=01)	—	500	—	μA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	

Table continues on the next page...

4. Crystal startup time is defined as the time between oscillator being enabled and OSCINIT bit in the MCG_S register being set.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

6.3.3 32 kHz oscillator electrical characteristics

6.3.3.1 32 kHz oscillator DC electrical specifications

Table 17. 32kHz oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{BAT}	Supply voltage	1.71	—	3.6	V
R_F	Internal feedback resistor	—	100	—	MΩ
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp}[1]	Peak-to-peak amplitude of oscillation	—	0.6	—	V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.3.2 32 kHz oscillator frequency specifications

Table 18. 32 kHz oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal	—	32.768	—	kHz	
t_{start}	Crystal start-up time	—	1000	—	ms	1
$v_{ec\_extal32}$	Externally provided input clock amplitude	700	—	V_{BAT}	mV	2, 3

1. Proper PC board layout procedures must be followed to achieve specifications.
2. This specification is for an externally supplied clock driven to EXTAL32 and does not apply to any other clock input. The oscillator remains enabled and XTAL32 must be left unconnected.
3. The parameter specified is a peak-to-peak value and V_{IH} and V_{IL} specifications do not apply. The voltage of the applied clock must be within the range of V_{SS} to V_{BAT}.

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

Table 20. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Swap Control execution time					
$t_{swapx01}$	- control code 0x01	—	200	—	μs	
$t_{swapx02}$	- control code 0x02	—	70	150	μs	
$t_{swapx04}$	- control code 0x04	—	70	150	μs	
$t_{swapx08}$	- control code 0x08	—	—	30	μs	
	Program Partition for EEPROM execution time					
$t_{pgmpart64k}$	- 64 KB FlexNVM	—	138	—	ms	
	Set FlexRAM Function execution time:					
$t_{setramff}$	- Control Code 0xFF	—	70	—	μs	
$t_{setram32k}$	- 32 KB EEPROM backup	—	0.8	1.2	ms	
$t_{setram64k}$	- 64 KB EEPROM backup	—	1.3	1.9	ms	
Byte-write to FlexRAM for EEPROM operation						
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	175	260	μs	3
	Byte-write to FlexRAM execution time:					
$t_{eewr8b32k}$	- 32 KB EEPROM backup	—	385	1800	μs	
$t_{eewr8b64k}$	- 64 KB EEPROM backup		475	2000	μs	
Word-write to FlexRAM for EEPROM operation						
$t_{eewr16bers}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
	Word-write to FlexRAM execution time:					
$t_{eewr16b32k}$	- 32 KB EEPROM backup	—	385	1800	μs	
$t_{eewr16b64k}$	- 64 KB EEPROM backup	—	475	2000	μs	
Longword-write to FlexRAM for EEPROM operation						
$t_{eewr32bers}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
	Longword-write to FlexRAM execution time:					
$t_{eewr32b32k}$	- 32 KB EEPROM backup	—	630	2050	μs	
$t_{eewr32b64k}$	- 64 KB EEPROM backup	—	810	2250	μs	

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

6.4.1.3 Flash high voltage current behaviors

Table 21. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 22. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
	Program Flash					
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2
	Data Flash					
$t_{nvmretd10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretd1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycd}$	Cycling endurance	10 K	50 K	—	cycles	2
	FlexRAM as EEPROM					
$t_{nvmretee100}$	Data retention up to 100% of write endurance	5	50	—	years	
$t_{nvmretee10}$	Data retention up to 10% of write endurance	20	100	—	years	
	Write endurance					3
$n_{nvmwree16}$	• EEPROM backup to FlexRAM ratio = 16	35 K	175 K	—	writes	
$n_{nvmwree128}$	• EEPROM backup to FlexRAM ratio = 128	315 K	1.6 M	—	writes	
$n_{nvmwree512}$	• EEPROM backup to FlexRAM ratio = 512	1.27 M	6.4 M	—	writes	
$n_{nvmwree4k}$	• EEPROM backup to FlexRAM ratio = 4096	10 M	50 M	—	writes	

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at -40 °C ≤ T_j ≤ °C.
3. Write endurance represents the number of writes to each FlexRAM location at -40 °C ≤Tj ≤ °C influenced by the cycling endurance of the FlexNVM (same value as data flash) and the allocated EEPROM backup per subsystem. Minimum and typical values assume all byte-writes to FlexRAM.

6.4.2 EzPort switching specifications

Table 23. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{SYS}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{SYS}/8$	MHz
EP2	$\overline{\text{EZP\_CS}}$ negation to next $\overline{\text{EZP\_CS}}$ assertion	2 x t_{EZP_CK}	—	ns
EP3	$\overline{\text{EZP\_CS}}$ input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to $\overline{\text{EZP\_CS}}$ input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—		ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	$\overline{\text{EZP\_CS}}$ negation to EZP_Q tri-state	—	12	ns

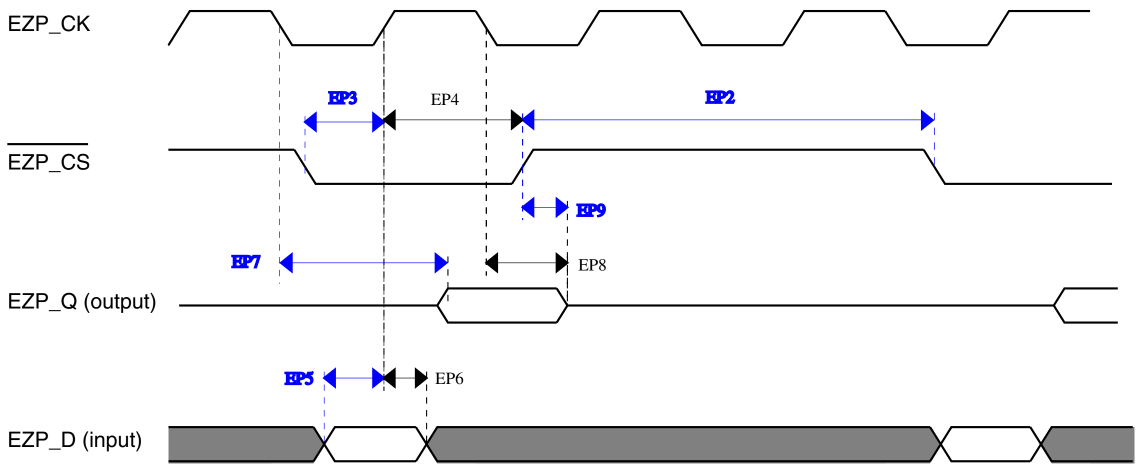

Figure 8. EzPort Timing Diagram

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

Table 26. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}–0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

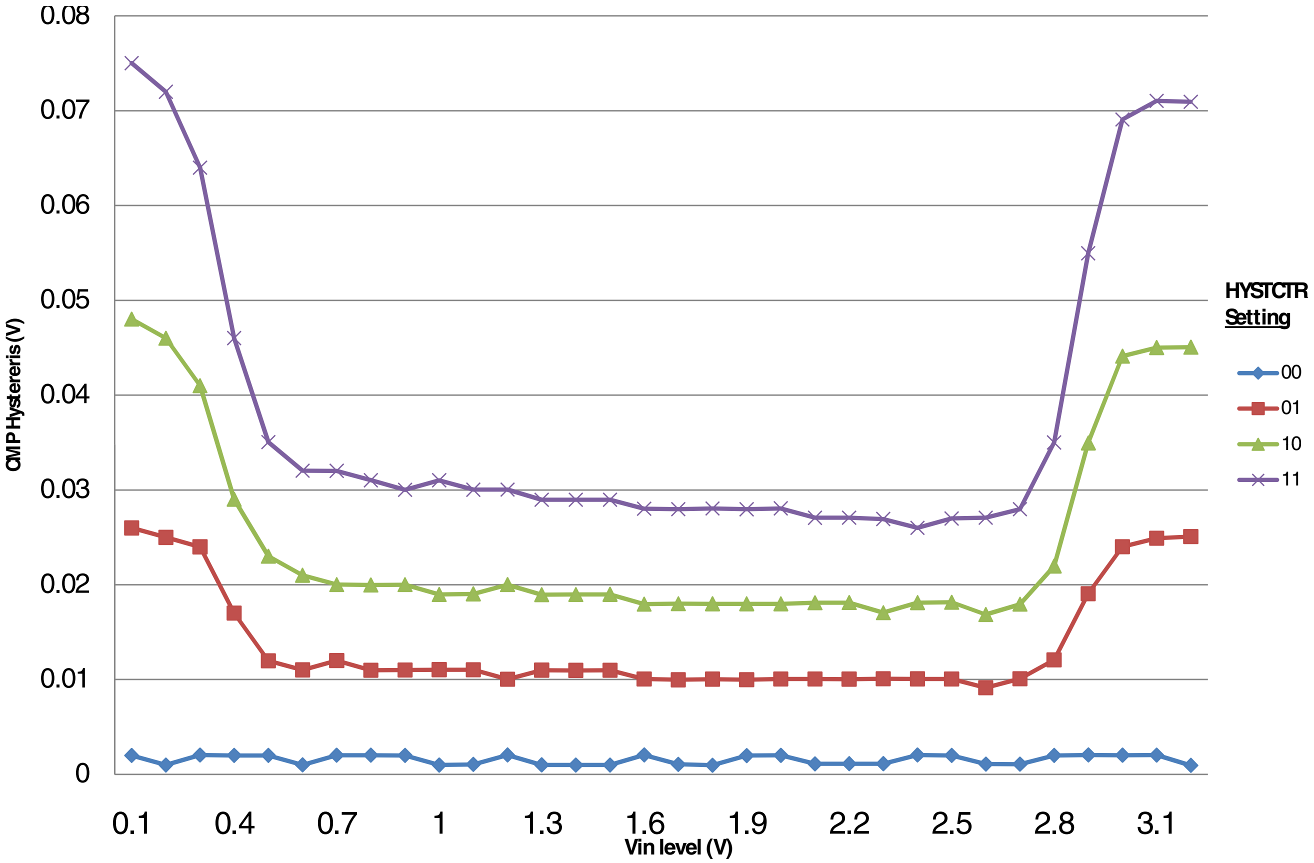

Figure 12. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

6.6.3.2 12-bit DAC operating behaviors

Table 28. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	330	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	1200	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2$ V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4$ V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance (load = 3 kΩ)	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h • High power (SP_{HP}) • Low power (SP_{LP})	 1.2 0.05	 1.7 0.12	 — —	V/μs	
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth • High power (SP_{HP}) • Low power (SP_{LP})	 550 40	 — —	 — —	kHz	

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with $V_{DDA} > 2.4$ V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

Table 30. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	1
V_{out}	Voltage reference output — factory trim	1.1584	—	1.2376	V	1
V_{out}	Voltage reference output — user trim	1.193	—	1.197	V	1
V_{step}	Voltage reference trim step	—	0.5	—	mV	1
V_{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range)	—	—	80	mV	1
I_{bg}	Bandgap only current	—	—	80	µA	1
ΔV_{LOAD}	Load regulation • current = ± 1.0 mA	—	200	—	µV	1, 2
T_{stup}	Buffer startup time	—	—	100	µs	
V_{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 31. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	°C	

Table 32. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim	1.173	1.225	V	

6.7 Timers

See General switching specifications.

6.8 Communication interfaces

1. Typical values assume VREGIN = 5.0 V, Temp = 25 °C unless otherwise stated.
2. Operating in pass-through mode: regulator output voltage equal to the input voltage minus a drop proportional to I_{Load}.

6.8.4 DSPI switching specifications (limited voltage range)

The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Table 35. Master mode DSPI timing (limited voltage range)

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	—	25	MHz	
DS1	DSPI_SCK output cycle time	2 x t_{BUS}	—	ns	
DS2	DSPI_SCK output high/low time	(t_{SCK}/2) − 2	(t_{SCK}/2) + 2	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	(t_{BUS} x 2) − 2	—	ns	1
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	(t_{BUS} x 2) − 2	—	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	—	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	−2	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	15	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

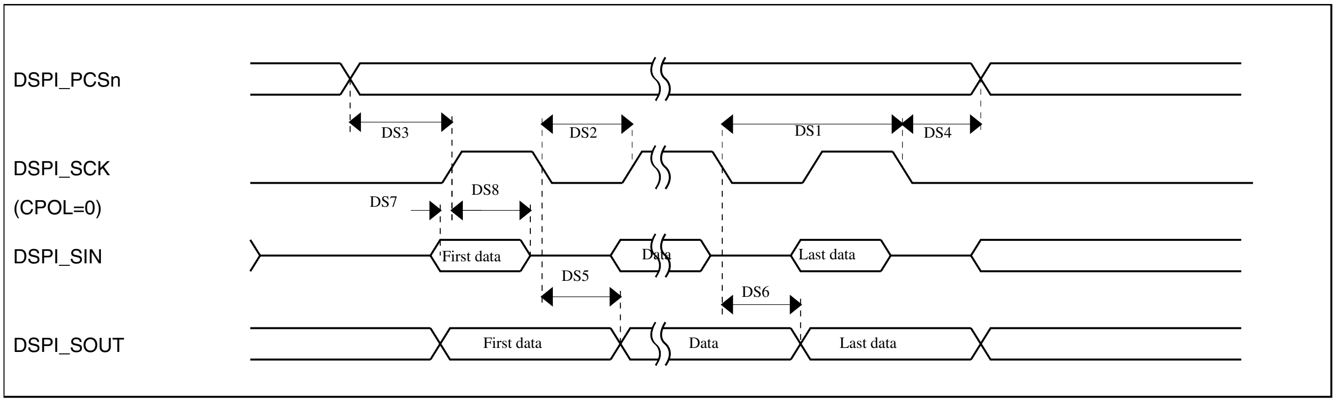

Figure 16. DSPI classic SPI timing — master mode

Table 37. Master mode DSPI timing (full voltage range) (continued)

Num	Description	Min.	Max.	Unit	Notes
DS2	DSPI_SCK output high/low time	$(t_{SCK}/2)$ - 4	$(t_{SCK/2})$ + 4	ns	
DS3	DSPI_PCS*n* valid to DSPI_SCK delay	$(t_{BUS}$ x 2) – 4	—	ns	2
DS4	DSPI_SCK to DSPI_PCS*n* invalid delay	$(t_{BUS}$ x 2) – 4	—	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	—	10	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-4.5	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	20.5	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.
2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

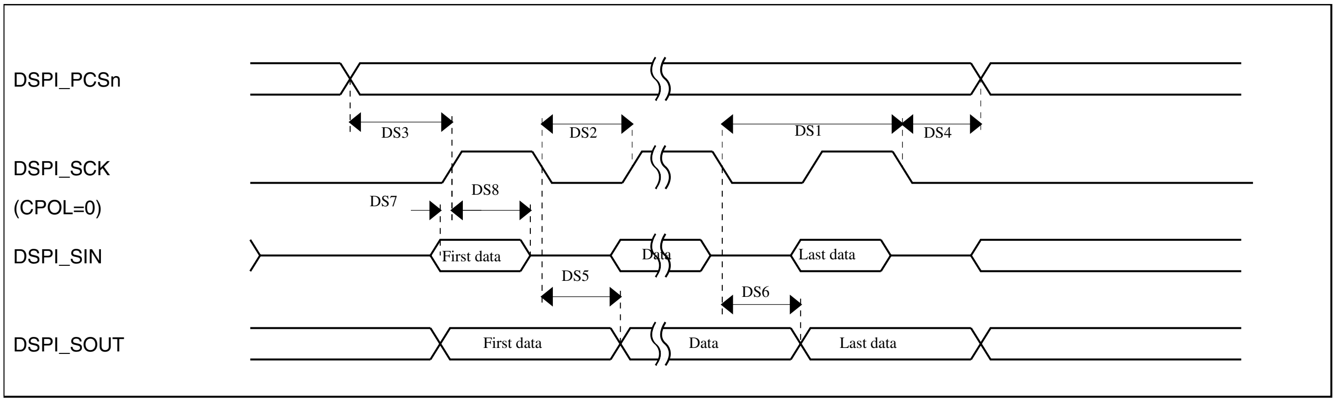

Figure 18. DSPI classic SPI timing — master mode

Table 38. Slave mode DSPI timing (full voltage range)

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	6.25	MHz
DS9	DSPI_SCK input cycle time	8 x t_{BUS}	—	ns
DS10	DSPI_SCK input high/low time	$(t_{SCK}/2)$ - 4	$(t_{SCK/2})$ + 4	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	20	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	$\overline{\text{DSPI\_SS}}$ active to DSPI_SOUT driven	—	19	ns
DS16	$\overline{\text{DSPI\_SS}}$ inactive to DSPI_SOUT not driven	—	19	ns

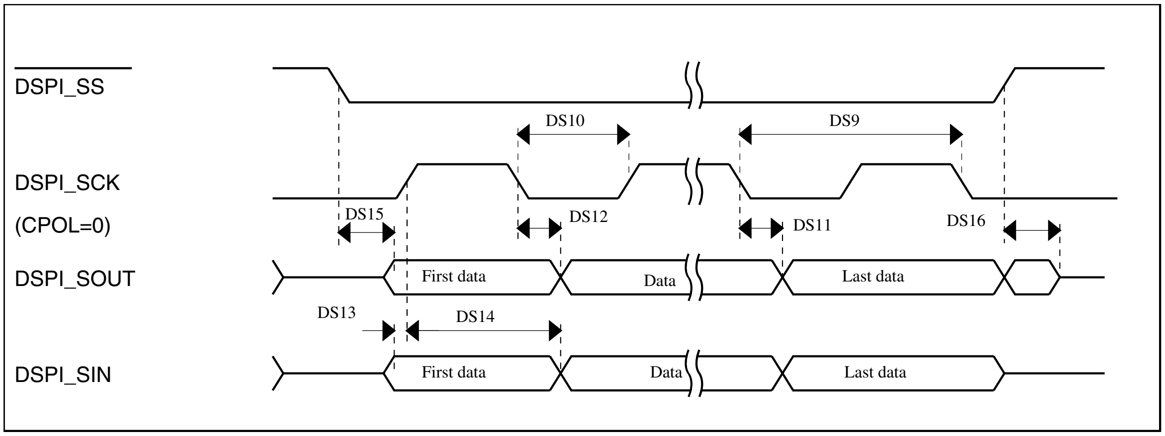

Figure 19. DSPI classic SPI timing — slave mode

6.8.6 I^{2}C switching specifications

See General switching specifications.

6.8.7 UART switching specifications

See General switching specifications.

6.8.8 Normal Run, Wait and Stop mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in Normal Run, Wait and Stop modes.

Table 39. I2S/SAI master mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	40	—	ns
S2	I2S_MCLK (as an input) pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	80	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	15	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	15	ns

Table continues on the next page...

Table 39. I2S/SAI master mode timing (continued)

Num.	Characteristic	Min.	Max.	Unit
S8	I2S_TX_BCLK to I2S_TXD invalid	0	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	25	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

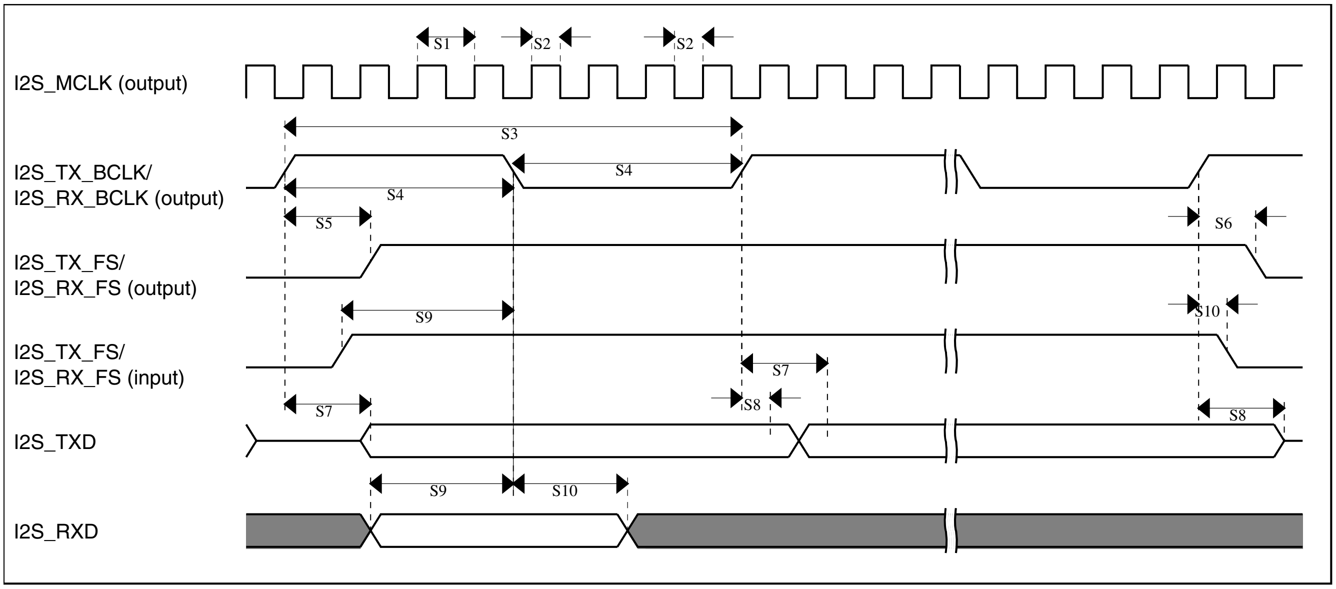

Figure 20. I2S/SAI timing — master modes

Table 40. I2S/SAI slave mode timing

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	10	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	29	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	10	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	21	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

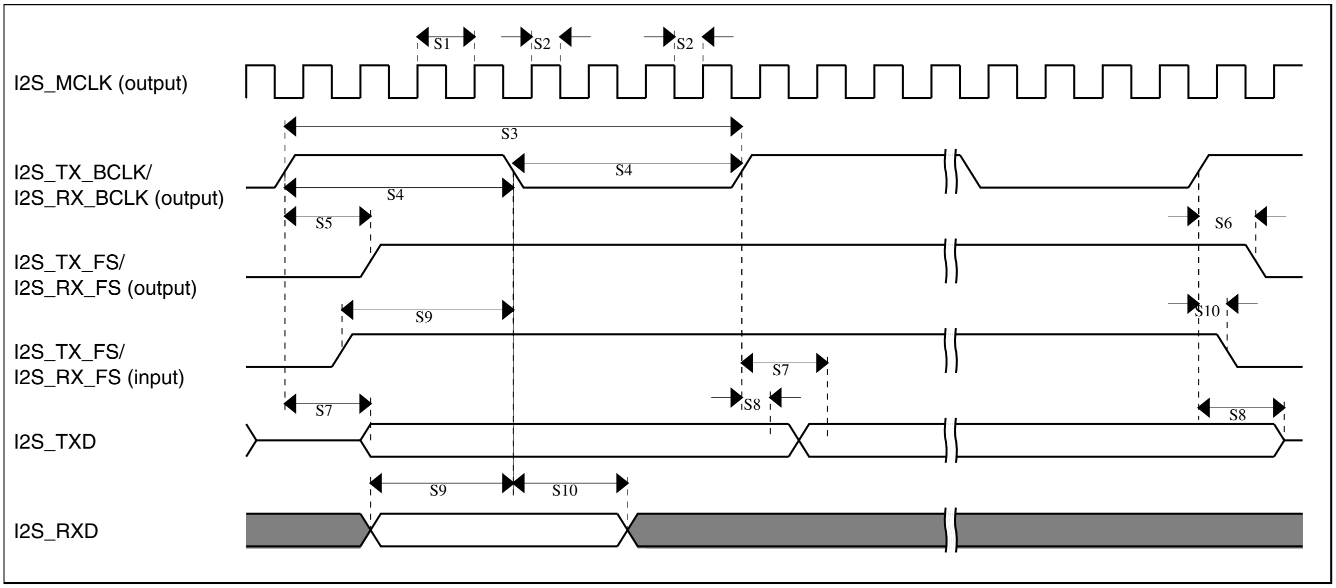

Figure 22. I2S/SAI timing — master modes

Table 42. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	87	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	72	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

80 LQFP	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
20	VSSA	VSSA								
21	VREF_OUT/ CMP1_IN5/ CMP0_IN5	VREF_OUT/ CMP1_IN5/ CMP0_IN5								
22	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23								
23	XTAL32	XTAL32								
24	EXTAL32	EXTAL32								
25	VBAT	VBAT								
26	JTAG_TCLK/ SWD_CLK/ EZP_CLK		PTA0	UART0_CTS_b/ UART0_COL_b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
27	JTAG_TDI/ EZP_DI		PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
28	JTAG_TDO/ TRACE_SWO/ EZP_DO		PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
29	JTAG_TMS/ SWD_DIO		PTA3	UART0_RTS_b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
30	NMI_b/ EZP_CS_b		PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
31	DISABLED		PTA5	USB_CLKIN	FTM0_CH2			I2S0_TX_BCLK	JTAG_TRST_b	
32	DISABLED		PTA12		FTM1_CH0			I2S0_TXD0	FTM1_QD_PHA	
33	DISABLED		PTA13/ LLWU_P4		FTM1_CH1			I2S0_TX_FS	FTM1_QD_PHB	
34	DISABLED		PTA14	SPI0_PCS0	UART0_TX			I2S0_RX_BCLK	I2S0_TXD1	
35	DISABLED		PTA15	SPI0_SCK	UART0_RX			I2S0_RXD0		
36	DISABLED		PTA16	SPI0_SOUT	UART0_CTS_b/ UART0_COL_b			I2S0_RX_FS	I2S0_RXD1	
37	DISABLED		PTA17	SPI0_SIN	UART0_RTS_b			I2S0_MCLK		
38	VDD	VDD								
39	VSS	VSS								
40	EXTAL0	EXTAL0	PTA18		FTM0_FLT2				FTM_CLKIN0	
41	XTAL0	XTAL0	PTA19		FTM1_FLT0			LPTMR0_ALT1	FTM_CLKIN1	
42	RESET_b	RESET_b								
43	ADC0_SE8	ADC0_SE8	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_PHA		
44	ADC0_SE9	ADC0_SE9	PTB1	I2C0_SDA	FTM1_CH1			FTM1_QD_PHB		
45	ADC0_SE12	ADC0_SE12	PTB2	I2C0_SCL	UART0_RTS_b			FTM0_FLT3		
46	ADC0_SE13	ADC0_SE13	PTB3	I2C0_SDA	UART0_CTS_b/ UART0_COL_b			FTM0_FLT0		
47	DISABLED		PTB10	SPI1_PCS0	UART3_RX			FTM0_FLT1		
48	DISABLED		PTB11	SPI1_SCK	UART3_TX			FTM0_FLT2		
49	DISABLED		PTB12	UART3_RTS_b	FTM1_CH0	FTM0_CH4		FTM1_QD_PHA		

80 LQFP	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
50	DISABLED		PTB13	UART3_CTS_b	FTM1_CH1	FTM0_CH5		FTM1_QD_PHB		
51	DISABLED		PTB16	SPI1_SOUT	UART0_RX			EWM_IN	FTM_CLKIN0	
52	DISABLED		PTB17	SPI1_SIN	UART0_TX			EWM_OUT_b	FTM_CLKIN1	
53	DISABLED		PTB18		FTM2_CH0	I2S0_TX_BCLK				
54	DISABLED		PTB19		FTM2_CH1	I2S0_TX_FS				
55	ADC0_SE14	ADC0_SE14	PTC0	SPI0_PCS4	PDB0_EXTRG			I2S0_TXD1		
56	ADC0_SE15	ADC0_SE15	PTC1/ LLWU_P6	SPI0_PCS3	UART1_RTS_b	FTM0_CH0		I2S0_TXD0		
57	ADC0_SE4b/ CMP1_IN0	ADC0_SE4b/ CMP1_IN0	PTC2	SPI0_PCS2	UART1_CTS_b	FTM0_CH1		I2S0_TX_FS		
58	CMP1_IN1	CMP1_IN1	PTC3/ LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2	CLKOUT	I2S0_TX_BCLK		
59	VSS	VSS								
60	VDD	VDD								
61	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	FTM0_CH3		CMP1_OUT		
62	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ALT2	I2S0_RXD0		CMP0_OUT	FTM0_CH2	
63	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_SOUT	PDB0_EXTRG	I2S0_RX_BCLK		I2S0_MCLK		
64	CMP0_IN1	CMP0_IN1	PTC7	SPI0_SIN	USB_SOF_OUT	I2S0_RX_FS				
65	CMP0_IN2	CMP0_IN2	PTC8			I2S0_MCLK				
66	CMP0_IN3	CMP0_IN3	PTC9			I2S0_RX_BCLK		FTM2_FLT0		
67	DISABLED		PTC10	I2C1_SCL		I2S0_RX_FS				
68	DISABLED		PTC11/ LLWU_P11	I2C1_SDA		I2S0_RXD1				
69	DISABLED		PTC12							
70	DISABLED		PTC13							
71	DISABLED		PTC16		UART3_RX					
72	DISABLED		PTC17		UART3_TX					
73	DISABLED		PTD0/ LLWU_P12	SPI0_PCS0	UART2_RTS_b					
74	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK	UART2_CTS_b					
75	DISABLED		PTD2/ LLWU_P13	SPI0_SOUT	UART2_RX	I2C0_SCL				
76	DISABLED		PTD3	SPI0_SIN	UART2_TX	I2C0_SDA				
77	ADC0_SE21	ADC0_SE21	PTD4/ LLWU_P14	SPI0_PCS1	UART0_RTS_b	FTM0_CH4		EWM_IN		
78	ADC0_SE6b	ADC0_SE6b	PTD5	SPI0_PCS2	UART0_CTS_b/ UART0_COL_b	FTM0_CH5		EWM_OUT_b		
79	ADC0_SE7b	ADC0_SE7b	PTD6/ LLWU_P15	SPI0_PCS3	UART0_RX	FTM0_CH6		FTM0_FLT0		
80	ADC0_SE22	ADC0_SE22	PTD7	CMT_IRO	UART0_TX	FTM0_CH7		FTM0_FLT1		